

### N-Channel 30-V Logic Level Enhancement Mode MOSFET

#### Description

MS17N03Q8 provides the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost effectiveness. The SOP-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

#### Features

- RDS(ON)=15mΩ(max.)@VGS=10V, ID=10A
- Simple drive requirement
- Low on-resistance
- Fast switching speed
- RoHS compliant package

Package type : SO-8

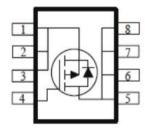
#### **Packing & Order Information**

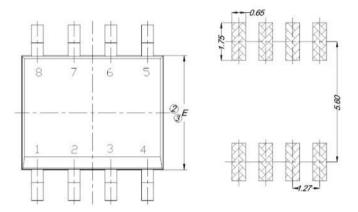
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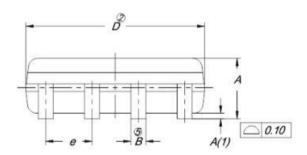


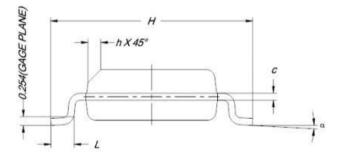


#### Graphic symbol









	N	ILLIMET	ERS	
DIM.	MIN.	NOM.	MAX	
А	1.35	1.55	1.75	
A(1)	0.10	0.18	0.25	
В	0.38	0.45	0.51	
C D E	0.19 4.80	0.22 4.90	0.25	
			5.00 4.00	
	3.80	3.90		
е		1.27 BSC		
н	5.80	6.00	6.20	
L	0.50	0.72 4°	0.93 8°	
α	0°			
h	0.25	0.38	0.50	



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### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)					
Symbol	Parameter	Value	Unit		
V <sub>DS</sub>	Drain-Source Voltage	30	V		
V <sub>G</sub> s	Gate-Source Voltage	±20	V		
T_	Drain Current -Continuous (TC=25°C)	10	А		
ID	Drain Current -Continuous (TC=100°C)	8	А		
I <sub>DM</sub>	Pulsed Drain Current (Note 1)	40	А		
I <sub>AS</sub>	Avalanche Current	12	А		
E <sub>AS</sub>	Avalanche Energy @ L=0.1mH , I_D=10A , $R_{\rm G}{=}25\Omega$	5	mJ		
E <sub>AR</sub>	Repetitive Avalanche Energy @ L=0.005mH (Note 2)	2.5	mJ		
P <sub>D</sub>	Power Dissipation ( $T_A=25^{\circ}C$ ) (Note 3)	3	W		
	Power Dissipation (T <sub>A</sub> =100°C)	1.5	W		
Tj/Tstg	Operating Junction and Storage Temperature Range	-55 to +175	°C		

100% UIS testing in condition of  $V_D$ =15V, L=0.1mH,  $V_G$ =10V, I<sub>L</sub>=10A, Rated  $V_{DS}$ =30V N-CH

Thermal Data				
Symbol	Parameter	Max.	Units	
R <sub>thj-c</sub>	Thermal Resistance, Junction-to-Case, max	25	°C/W	
R <sub>thj-a</sub>	Thermal Resistance, Junction-to-Ambient, max	50*3	°C/W	

Note:

1. Pulse width limited by maximum junction temperature.

2. Duty cycle≤1%

3. Surface mounted on 1 in 2 copper pad of FR-4 board, 125°C/W when mounted on minimum copper pad.

Characteristics (Tj=25°C, unless otherwise specified)					
Symbol	Test Conditions	Min	Typ.	Max.	Units
$V_{GS(th)}$	$V_{\rm DS}=V_{\rm GS},I_{\rm D}=250\mu A$	1	1.5	3	V
BV <sub>DSS</sub>	$V_{\rm GS}=0~V$ , $I_{\rm D}=250\mu A$	30			V
G <sub>FS</sub> *1	$V_{DS} = 5 V, I_D = 10 A$		80		S
I <sub>GSS</sub>	$V_{GS} = \pm 20$			±100	nA
Idss	$\label{eq:VDS} \begin{array}{l} V_{DS} = 24 \ V \mbox{, } V_{GS} = 0 \ V \\ V_{DS} = 20 \ V \mbox{, } V_{GS} = 0 \ V \mbox{, } T_j = 125 \mbox{``C} \end{array}$			10 25	uA
I <sub>D(ON)</sub> *1	$V_{GS} = 10 V$ , $I_D = 10 A$	10			A
R <sub>DS(ON)</sub> *1	$V_{GS} = 10 V$ , $I_D = 10 A$		13	15	mΩ
	$V_{GS} = 4.5 \ V \ , \ I_D = 6 \ A$		20	25	



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Dynamic					
Symbol	Test Conditions	Min	Typ.	Max.	Units
Qg(VGS=10V) *1.2	$V_{DS} = 15 V, I_D = 10 A, V_{GS} = 10 V$		11		nC
$Q_{gs}(V_{GS}=4.5V)$ *1.2			6		nC
Q <sub>gs</sub> *1.2			1.2		nC
Q <sub>gd</sub> *1.2			3.3		nC
td(on) *1.2			11		ns
t <sub>r</sub> *1.2	$V_{DS} = 15 V, I_D = 1 A, V_{GS} = 10 V$		16		ns
t <sub>d(off)</sub> *1.2	$R_G = 25 \ \Omega$ , $R_D = 15 \ \Omega$		36		ns
tf *1.2			20		ns
CISS			1115		pF
Coss	$V_{DS} = 15$ V, $V_{GS} = 0$ V, $f = 1.0$ MHz		116		pF
C <sub>RSS</sub>			82		pF
Rg	$V_{DS} = 15 \text{mV}, V_{GS} = 0 \text{ V}, f = 1.0 \text{MHz}$		2		Ω

Source-Drain Diode					
Symbol	Test Conditions	Min	Typ.	Max.	Units
Is *1				2.3	
I <sub>SM</sub> *3				9.2	A
V <sub>SD</sub> *1	$I_F = I_S$ , $V_{\rm GS} = 0~V$			102	V
t <sub>rr</sub>	L L 11/1/ 1000//		50		ns
Qrr	$I_F = I_S$ , $dI/dt = 100 A/\mu s$		2		uC

Notes:

1. Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2\%$ .

2. Independent of operating temperature.

3. Pulse width limited by maximum junction temperature.



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